TOSHIBA TLP330

TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

TLP330

PROGRAMMABLE CONTROLLERS

AC/DC-INPUT MODULE

TELECOMMUNICATION

The TOSHIBA TLP330 consists of a photo-transistor optically coupled to two gallium arsenide infrared emitting diode connected inverse parallel in a six lead plastic DIP package. This is suitable for application of AC input current up to 150mA.

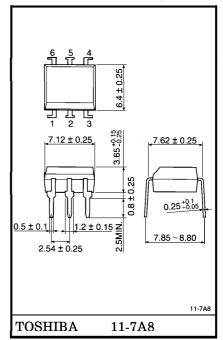
I_F Maximum Rating : ±150mA
 Collector-Emitter Voltage : 55V (Min.)

• Current Transfer Ratio : 25% (Min.) ($I_F = \pm 20$ mA)

• Isolation Voltage : 5000Vrms (Min.)

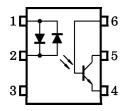
• UL Recognized : UL1577, File No. E67349

Unit in mm



Weight: 0.39g

PIN CONFIGURATIONS (TOP VIEW)



1 : ANODE, CATHODE 2 : CATHODE, ANODE

3 : NC 4 : EMITTER

5 : COLLECTOR

6: BASE

MAXIMUM RATINGS (Ta = 25°C)

	CHARACTERISTIC	SYMBOL	RATING	UNIT
	Forward Current	$I_{\mathbf{F}}$	±150	mA
B	Forward Current Derating (Ta≥25°C)	ΔI _F /°C	-1.5	mA/°C
LED	Peak Forward Current (100 µs pulse, 100 pps)	I_{FP}	±1	A
	Junction Temperature	Tj	125	°C
	Collector-Emitter Voltage	v_{CEO}	55	V
ده	Collector-Base Voltage	v_{CBO}	80	V
OR	Emitter-Collector Voltage	v_{ECO}	7	V
CT	Emitter-Base Voltage	v_{EBO}	7	V
DETE	Collector Current	$I_{\mathbf{C}}$	80	mA
DE	Power Dissipation	PC	150	mW
	Power Dissipation Derating (Ta≥25°C)	ΔP _C /°C	-1.5	mW/°C
	Junction Temperature		125	°C
Storage Temperature Range		$T_{ m stg}$	-55~125	°C
Оре	erating Temperature Range	$T_{ m opr}$	-55~100	°C
Lea	d Soldering Temperature (10s)	T _{sol}	260	°C
Tot	al Package Power Dissipation	P_{T}	250	mW
Tot	al Package Power Dissipation Derating (Ta≥25°C)	$\Delta P_{T} / ^{\circ}C$	-2.5	mW/°C
Isol	ation Voltage (AC, 1 min, R.H.≤60%) (Note 1)	$BV_{\mathbf{S}}$	5000	Vrms

(Note 1) Device considered a two terminal device: Pins 1, 2 and 3 shorted together and pins 4, 5 and 6 shorted together.

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	v_{CC}	1	5	24	V
Forward Current	I _{F (RMS)}	l	20	120	mA
Collector Current	$I_{\mathbf{C}}$		1	10	mA
Operating Temperature	$\mathrm{T}_{\mathrm{opr}}$	-25	_	85	$^{\circ}\mathrm{C}$

INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

	CHARACTERISTIC	SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	$ m V_{ m F}$	$I_{ m F}=\pm 100{ m mA}$	_	1.4	1.7	V
	Forward Current	$I_{\mathbf{F}}$	$V_{\mathbf{F}} = \pm 0.7 V$	_	2.5	20	μ A
	Capacitance	C_{T}	V=0, $f=1MHz$	_	100	_	рF
	Collector-Emitter Breakdown Voltage	V (BR) CEO	$I_{ m C}\!=\!0.5{ m mA}$	55	_	_	V
	Emitter-Collector Breakdown Voltage	V (BR) ECO	$I_{ extbf{E}}\!=\!0.1 ext{mA}$	7	_	_	V
DETECTOR	Collector-Base Breakdown Voltage	V (BR) CBO	$I_{\text{C}} = 0.1 \text{mA}$	80	_	_	V
	Emitter-Base Breakdown Voltage	V (BR) EBO	$I_{ extbf{E}}\!=\!0.1 ext{mA}$	7	_	_	V
EC	Collector Dark Current ICEO	Igno	$V_{ m CE}$ = 24 V		10	100	nA
ET	Conector Dark Current	$_{ m ICEO}$	$V_{ ext{CE}} = 24V$, $Ta = 85^{\circ}C$	_	2	50	μ A
	Collector Dark Current	I_{CER}	$V_{\text{CE}} = 24V$, $Ta = 85^{\circ}\text{C}$ $R_{\text{BE}} = 1M\Omega$	_	0.5	10	μ A
	Collector Dark Current	I_{CBO}	$V_{CB} = 10V$		0.1	_	nA
	DC Forward Current Gain	$h_{ extbf{FE}}$	$V_{CE} = 5V, I_{C} = 0.5 \text{mA}$	_	400	_	_
	Capacitance (Collector to Emitter)	CCE	V=0, f=1MHz		10	_	pF

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT
Current Transfer Ratio	I_C/I_F	$I_F = \pm 20 \text{mA V}_{CE} = 1 \text{V}$	25	_	_	%
	$I_{C}/I_{F(high)}$	$I_F = \pm 100 \text{mA} \ V_{CE} = 1 \text{V}$	20	_	80	%
Base Photo-Current	I_{PB}	$V_F = \pm 5$ mA, $V_{CB} = 5$ V	_	10	_	μ A
Collector-Emitter	Var	$I_{C} = 2.4 \text{mA}, I_{F} = 20 \text{mA}$		_	0.4	V
Saturation Voltage	VCE (sat)	$I_{C} = 2.4 \text{mA}, I_{F} = \pm 100 \text{mA}$	_	_	0.4]
Off-State Collecter Current	I _{C (off)}	$V_{F} = \pm 0.7V, \ V_{CE} = 24V$	_	1	10	μ A
CTR Symmetry	I _{C (ratio)}	$I_{C}(I_{F} = -20 \text{mA})$ / $I_{C}(I_{F} = +20 \text{mA})$	0.5	1	2	_

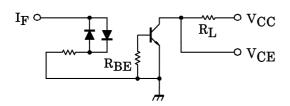
ISOLATION CHARACTERISTICS (Ta = 25°C)

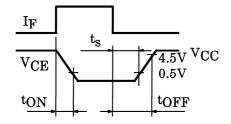
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capacitance (Input to Output)	c_{S}	V_S =0, f=1MHz	_	0.8	_	pF
Isolation Resistance	$R_{\mathbf{S}}$	V _S =500V, R.H.≦60%	5×10^{10}	10^{14}	_	Ω
		AC, 1 minute	5000	_		Vrms
Isolation Voltage	$\mathrm{BV}_{\mathbf{S}}$	AC, 1 second, in oil	_	10000	_	Vrms
		DC, 1 minute, in oil	_	10000	_	Vdc

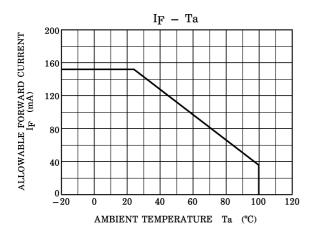
SWITCHING CHARACTERISTICS (Ta = 25°C)

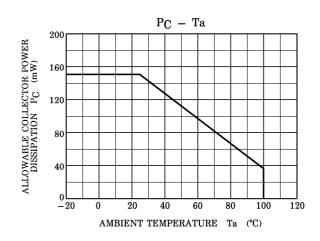
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Rise Time	${ m t_r}$	$V_{CC}=10V$ $I_{C}=2mA$ $R_{L}=100\Omega$	_	2	_	
Fall Time	t_f			3	_	
Turn-on Time	t_{on}		_	3	_	μ s
Turn-off Time	$t_{ m off}$		_	3	_	
Turn-on Time	$t_{ m ON}$	$R_L = 1.9 \text{k}\Omega \text{ (Fig.1)}$ $R_{BE} = \text{OPEN}$ $V_{CC} = 5 \text{V, I}_F = \pm 16 \text{mA}$	_	2	_	
Storage Time	$t_{\mathtt{S}}$		_	15	_	μ s
Turn-off Time	tOFF		_	25	_	
Turn-on Time	toN	$R_L = 1.9 k\Omega \text{ (Fig.1)}$ $R_{BE} = 220 k\Omega$ $V_{CC} = 5 \text{V, I}_F = \pm 16 \text{mA}$	_	2	_	
Storage Time	$t_{\mathtt{S}}$		_	12	_	μ s
Turn-off Time	tOFF		_	20	_	

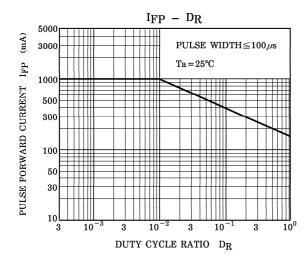
Fig.1 Switching Time Test Circuit

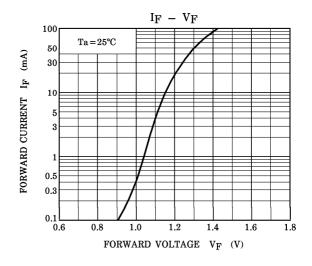


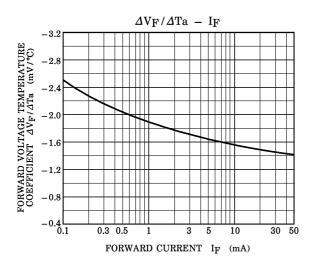


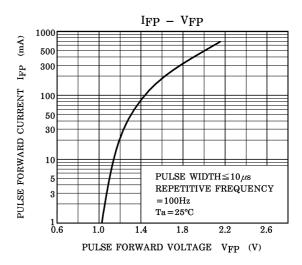












RESTRICTIONS ON PRODUCT USE

000707EBC

- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- Gallium arsenide (GaAs) is a substance used in the products described in this document. GaAs dust and fumes are toxic. Do not break, cut or pulverize the product, or use chemicals to dissolve them. When disposing of the products, follow the appropriate regulations. Do not dispose of the products with other industrial waste or with domestic garbage.
- The products described in this document are subject to the foreign exchange and foreign trade laws.
- ◆ The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.